

L Number	Hits	Search Text	DB	Time stamp
25	773387	h011021\$.ipc. c23c016\$.ipc.	USPAT; EPO; JPO; DERWENT	2002/11/16 21:05
26	39022	(h011021\$.ipc. c23c016\$.ipc.) and dry\$3	USPAT; EPO; JPO; DERWENT	2002/11/16 21:09
27	5072	(h011021\$.ipc. c23c016\$.ipc.) and (dry\$3 same heat\$3)	USPAT; EPO; JPO; DERWENT	2002/11/16 21:07
28	34	((h011021\$.ipc. c23c016\$.ipc.) and (dry\$3 same heat\$3)) and (cluster adj tool)	USPAT; EPO; JPO; DERWENT	2002/11/16 21:07
29	296	(h011021\$.ipc. c23c016\$.ipc.) and (dry\$3 adj (chamber vessel))	USPAT; EPO; JPO; DERWENT	2002/11/16 21:33
30	16	(h011021\$.ipc. c23c016\$.ipc.) and ((dry\$3 adj (chamber vessel)) with transport\$3)	USPAT; EPO; JPO; DERWENT	2002/11/16 21:24
31	60	(h011021\$.ipc. c23c016\$.ipc.) and ((dry\$3 adj (chamber vessel)) with heat\$3)	USPAT; EPO; JPO; DERWENT	2002/11/16 21:24
32	92	(h011021\$.ipc. c23c016\$.ipc.) and ((dry\$3 adj (chamber vessel)) same heat\$3)	USPAT; EPO; JPO; DERWENT	2002/11/16 21:24
33	89	((h011021\$.ipc. c23c016\$.ipc.) and ((dry\$3 adj (chamber vessel)) same heat\$3)) not (((h011021\$.ipc. c23c016\$.ipc.) and (dry\$3 same heat\$3)) and (cluster adj tool))	USPAT; EPO; JPO; DERWENT	2002/11/16 21:24
34	7	(h011021\$.ipc. c23c016\$.ipc.) and (dry\$3 adj (chamber vessel)) and polish\$3 and (clean\$3 wash\$3 rinse\$4)	USPAT; EPO; JPO; DERWENT	2002/11/16 21:39
35	233	(dry\$3 adj (chamber vessel)) and polish\$3 and (clean\$3 wash\$3 rinse\$4)	USPAT; EPO; JPO; DERWENT	2002/11/16 21:39
36	57	((dry\$3 adj (chamber vessel)) and polish\$3 and (clean\$3 wash\$3 rinse\$4)) and (semiconductor\$)	USPAT; EPO; JPO; DERWENT	2002/11/16 21:59
37	50	((dry\$3 adj (chamber vessel)) and polish\$3 and (clean\$3 wash\$3 rinse\$4)) and (semiconductor\$) not (h011021\$.ipc. c23c016\$.ipc.) and (dry\$3 adj (chamber vessel)) and polish\$3 and (clean\$3 wash\$3 rinse\$4))	USPAT; EPO; JPO; DERWENT	2002/11/16 21:40
38	36	((dry\$3 adj (chamber vessel)) and polish\$3 and (clean\$3 wash\$3 rinse\$4)) and "CVD" (vapor adj deposit\$3) (film adj forming)	USPAT; EPO; JPO; DERWENT	2002/11/16 22:00
39	20	((dry\$3 adj (chamber vessel)) and polish\$3 and (clean\$3 wash\$3 rinse\$4)) and ("CVD" (vapor adj deposit\$3) (film adj forming\$3) not ((dry\$3 adj (chamber vessel)) and polish\$3 and (clean\$3 wash\$3 rinse\$4)) and (semiconductor\$) not ((h011021\$.ipc. c23c016\$.ipc.) and (dry\$3 adj (chamber vessel)) and polish\$3 and	USPAT; EPO; JPO; DERWENT	2002/11/16 22:00